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Amendments to the Abstract:

~~The present invention provides a display device which can reduce the~~ The irregularities of characteristics of a pair of transistors<sub>1</sub> which are prepared by a pseudo single crystallizing technique ~~and are used in a differential amplifying circuit or the like, are reduced.~~ To achieve this, semiconductor layers are formed on a substrate and ~~having~~ have pseudo single crystal regions therein, and a plurality of thin film ~~transistor-transistors~~ are arranged in the inside of the pseudo single crystal regions. ~~Out of the plurality of thin film transistors, two~~ Two or more of the plurality of thin film transistors<sub>1</sub> which are required to exhibit small irregularities relative to each other as ~~the characteristics of the transistors thereof,~~ have the direction of a the length of the gates of the respective thin film transistors arranged ~~with~~ at an inclination of within  $\pm 20$  degree with respect to the longitudinal direction of the strip-like grown crystals<sub>1</sub> and they are arranged such that, when channel regions of ~~the~~ respective thin film transistors are imaginarily extended in parallel to the growth direction of the strip-like grown crystals, at least portions of the channel regions are ~~superpose~~ superposed on each other.